Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



Marking code: Q063

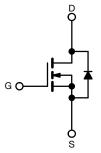
PRODUCT SUMMARY			
V _{DS} (V)	40		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0040		
I _D (A) ^e	92		
Configuration	Single		
Package	PowerPAK 1212-8SLW		

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- · Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40		
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current e	T _C = 25 °C	- I _D	92		
	T _C = 125 °C		53		
Continuous source current (diode conduction) e		I _S	54	А	
Pulsed drain current ^{a, e}		I _{DM}	282		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	24		
Single pulse avalanche energy	L = U. I IIIH	E _{AS}	28	mJ	
Maximum power dissipation b, e	T _C = 25 °C	$\begin{array}{c c} T_C = 25 \text{ °C} \\ \hline T_C = 125 \text{ °C} \end{array} \qquad P_D$	60	W	
	T _C = 125 °C		20		
Operating junction and storage temperature range Soldering recommendations (peak temperature) c		T _J , T _{stg}	-55 to +175	°C	
			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	81	°C/W	
Junction-to-case (drain) ^d		R_{thJC}	2.5		

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. See solder profile (www.vishay.com/doc?73257). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- c. When mounted on 1" square PCB (FR4 material)
- d. As per JESD51-14
- e. Values based on RthJC and TC of 25 °C.Actual values achievable will be dependent on the thermal characteristics of the complete system

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.5	3.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	20	-	-	Α
Drain-source on-state resistance a		V _{GS} = 10 V	I _D = 10 A	-	0.0032	0.0040	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0059	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0071	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		-	54	-	S
Dynamic ^b		•			1		
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1569	2197	
Output capacitance	C _{oss}	V _{GS} = 0 V		-	550	770	pF
Reverse transfer capacitance	C _{rss}			-	39	55	
Total gate charge ^c	Qg		V _{DS} = 20 V, I _D = 3 A	-	27	41	nC
Gate-source charge c	Q _{gs}	V _{GS} = 10 V		-	8	-	
Gate-drain charge c	Q _{gd}			-	6	-	
Gate resistance	R_g	f = 1 MHz		0.8	1.6	2.4	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V}, \text{ R}_L = 6.67 \Omega$ $I_D \cong 3 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	18	ns
Rise time ^c	t _r			-	4	8	
Turn-off delay time ^c	t _{d(off)}			-	21	32	
Fall time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Charac	teristic ^b	•			1		
Pulsed current ^a	I _{SM}			-	-	282	А
Forward voltage	V_{SD}	I _F = 10 A, V _{GS} = 0 V		-	0.82	1.1	V
Body diode reverse recovery time	t _{rr}	V_{DD} = 32 V, I_{FM} = 3 A, di/dt = 100 A/μs, R = 10 Ω , L = 0.3 mH, pulse width = 2 μs		-	30	60	ns
Body diode reverse recovery charge	Q _{rr}			-	23	46	nC
Reverse recovery fall time	ta			-	16	-	ns
Reverse recovery rise time	t _b			-	15	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.4	-	Α

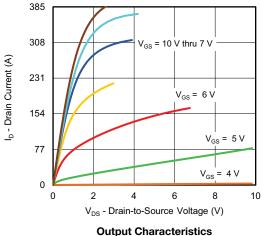
Notes

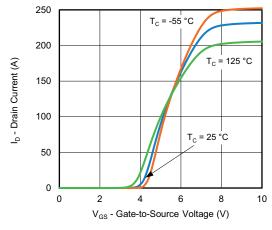
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

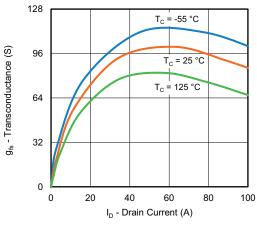


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

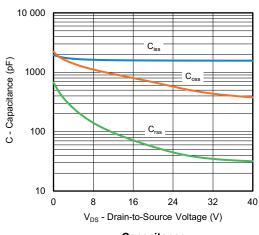




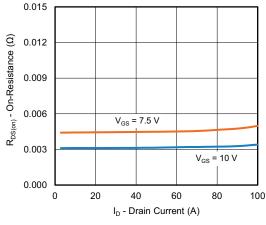
Transfer Characteristics



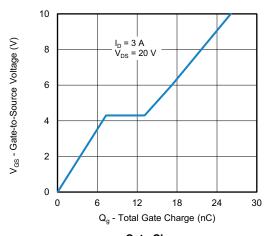
Transconductance



Capacitance



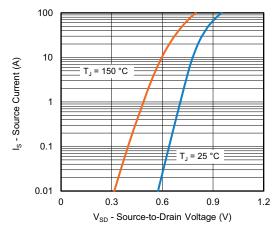
On-Resistance vs. Drain Current



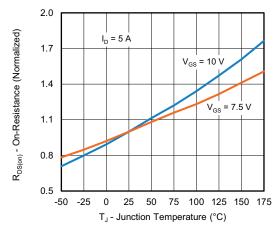
Gate Charge



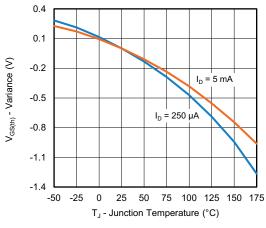
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



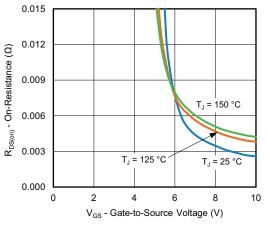
Source Drain Diode Forward Voltage



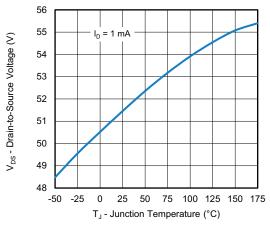
On-Resistance vs. Junction Temperature



Threshold Voltage



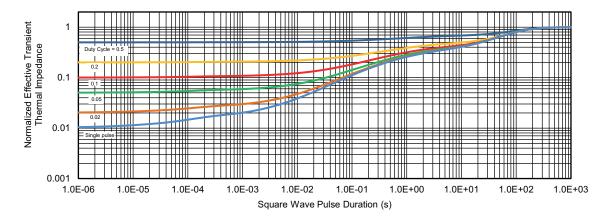
On-Resistance vs. Gate-to-Source Voltage



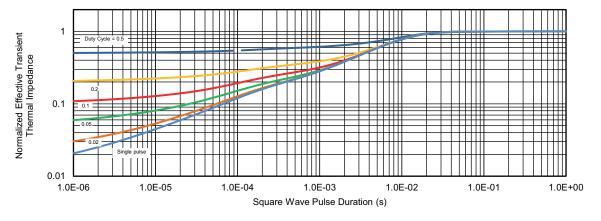
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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